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### What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

### Applications of "[Embedded - Microcontrollers](#)"

#### Details

Product Status	Active
Core Processor	e200z0h
Core Size	32-Bit Single-Core
Speed	64MHz
Connectivity	CANbus, LINbus, SPI, UART/USART
Peripherals	DMA, POR, PWM, WDT
Number of I/O	49
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	64K x 8
RAM Size	80K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 3.6V
Data Converters	A/D 16x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/stmicroelectronics/spc56ap60l3beabr">https://www.e-xfl.com/product-detail/stmicroelectronics/spc56ap60l3beabr</a>

SPC56xP54x/SPC56xP60x is present on the market in two different options enabling different features: Full-featured, and Airbag configuration. [Table 3](#) shows the main differences between the two versions.

**Table 3. SPC56xP54x/SPC56xP60x device configuration difference**

Feature	Enhanced Full-featured	Full-featured	Airbag
FlexCAN (controller area network)	3	2	2
CTU (cross triggering unit)	Yes		No
FlexRay	Yes (64 message buffer)		No
DSPI (deserial serial peripheral interface) modules	5		4
CRC (cyclic redundancy check) unit	2		1

## 1.4 Block diagram

[Figure 1](#) shows a top-level block diagram of the SPC56xP54x/SPC56xP60x MCU. [Table 4](#) summarizes the functions of the blocks.

The crossbar provides the following features:

- 6 master ports:
  - 2 e200z0 core complex Instruction ports
  - 2 e200z0 core complex Load/Store Data ports
  - eDMA
  - FlexRay
- 6 slave ports:
  - 2 Flash memory (code flash and data flash)
  - 2 SRAM (48 KB + 32 KB)
  - 2 PBRIDGE
- 32-bit internal address, 32-bit internal data paths
- Fixed Priority Arbitration based on Port Master
- Temporary dynamic priority elevation of masters

### 1.5.3 Enhanced direct memory access (eDMA)

The enhanced direct memory access (eDMA) controller is a second-generation module capable of performing complex data movements via 16 programmable channels, with minimal intervention from the host processor. The hardware micro architecture includes a DMA engine which performs source and destination address calculations, and the actual data movement operations, along with an SRAM-based memory containing the transfer control descriptors (TCD) for the channels. This implementation is utilized to minimize the overall block size.

The eDMA module provides the following features:

- 16 channels support independent 8, 16 or 32-bit single value or block transfers
- Supports variable sized queues and circular queues
- Source and destination address registers are independently configured to post-increment or remain constant
- Each transfer is initiated by a peripheral, CPU, or eDMA channel request
- Each eDMA channel can optionally send an interrupt request to the CPU on completion of a single value or block transfer
- DMA transfers possible between system memories, DSPIs, ADC, eTimer and CTU
- Programmable DMA Channel Multiplexer for assignment of any DMA source to any available DMA channel with up to 30 potential request sources
- eDMA abort operation through software

### 1.5.4 On-chip flash memory with ECC

The SPC56xP54x/SPC56xP60x provides up to 1024 KB of programmable, non-volatile, flash memory. The non-volatile memory (NVM) can be used for instruction and/or data storage. The flash memory module interfaces the system bus to a dedicated flash memory array controller. It supports a 32-bit data bus width at the system bus port, and a 128-bit read data interface to flash memory. The module contains a four-entry, 4x128-bit prefetch buffers. Prefetch buffer hits allow no-wait responses. Normal flash memory array accesses are registered and are forwarded to the system bus on the following cycle, incurring 2 wait states.

allow the appropriate priorities for each source of interrupt request, the priority of each interrupt request is software configurable.

When multiple tasks share a resource, coherent accesses to that resource need to be supported. The INTC supports the priority ceiling protocol for coherent accesses. By providing a modifiable priority mask, the priority can be raised temporarily so that all tasks which share the resource can not preempt each other.

The INTC provides the following features:

- Unique 9-bit vector for each separate interrupt source
- 8 software triggerable interrupt sources
- 16 priority levels with fixed hardware arbitration within priority levels for each interrupt source
- Ability to modify the ISR or task priority.
  - Modifying the priority can be used to implement the Priority Ceiling Protocol for accessing shared resources.
- 2 external high priority interrupts directly accessing the main core and IOP critical interrupt mechanism

The INTC module is replicated for each processor.

### 1.5.7 System clocks and clock generation

The following list summarizes the system clock and clock generation on the SPC56xP54x/SPC56xP60x:

- Lock detect circuitry continuously monitors lock status
- Loss of clock (LOC) detection for PLL outputs
- Programmable output clock divider ( $\div 1$ ,  $\div 2$ ,  $\div 4$ ,  $\div 8$ )
- Programmable output clock divider ( $\div 1$ ,  $\div 2$ ,  $\div 3$  to  $\div 256$ )
- eTimer module running at the same frequency as the e200z0h core
- On-chip oscillator with automatic level control
- Internal 16 MHz RC oscillator for rapid start-up and safe mode
  - Supports frequency trimming by user application

### 1.5.8 Frequency modulated phase-locked loop (FMPLL)

The FMPLL allows the user to generate high speed system clocks from a 4 MHz to 40 MHz input clock. Further, the FMPLL supports programmable frequency modulation of the system clock. The FMPLL multiplication factor, output clock divider ratio are all software configurable.

The FMPLL has the following major features:

- Input clock frequency from 4 MHz to 40 MHz
- Voltage controlled oscillator (VCO) range from 256 MHz to 512 MHz
- Reduced frequency divider (RFD) for reduced frequency operation without forcing the PLL to relock
- Modulation enabled/disabled through software

It implements the following features:

- Double buffered trigger generation unit with up to eight independent triggers generated from external triggers
- Trigger generation unit configurable in sequential mode or in triggered mode
- Each Trigger can be appropriately delayed to compensate the delay of external low pass filter
- Double buffered global trigger unit allowing eTimer synchronization and/or ADC command generation
- Double buffered ADC command list pointers to minimize ADC-trigger unit update
- Double buffered ADC conversion command list with up to 24 ADC commands
- Each trigger has the capability to generate consecutive commands
- ADC conversion command allows to control ADC channel from each ADC, single or synchronous sampling, independent result queue selection

### 1.5.26 Cyclic redundancy check (CRC)

- 3 contexts for the concurrent CRC computation
- Separate CRC engine for each context
- Zero-wait states during the CRC computation (pipeline scheme)
- 3 hard-wired polynomials (CRC-8 VDA CAN, CRC-32 Ethernet and CRC-16-CCITT)
- Support for byte/half-word/word width of the input data stream
- Support for expected and actual CRC comparison

### 1.5.27 Nexus development interface (NDI)

The NDI block provides real-time development support capabilities for the SPC56xP54x/SPC56xP60x Power Architecture based MCU in compliance with the IEEE-ISTO 5001-2003 standard. This development support is supplied for MCUs without requiring external address and data pins for internal visibility. The NDI block is an integration of several individual Nexus blocks that are selected to provide the development support interface for this device. The NDI block interfaces to the host processor and internal buses to provide development support as per the IEEE-ISTO 5001-2003 Class 2+ standard. The development support provided includes access to the MCU's internal memory map and access to the processor's internal registers during run time.

The Nexus Interface provides the following features:

- Configured via the IEEE 1149.1
- All Nexus port pins operate at  $V_{DDIO}$  (no dedicated power supply)
- Nexus 2+ features supported
  - Static debug
  - Watchpoint messaging
  - Ownership trace messaging
  - Program trace messaging
  - Real time read/write of any internally memory mapped resources through JTAG pins
  - Overrun control, which selects whether to stall before Nexus overruns or keep executing and allow overwrite of information

Table 5. Supply pins (continued)

Supply		Pin		
Symbol	Description	LQFP 100	LQFP 144	LQFP 176 <sup>(1)</sup>
V <sub>SS_LV_COR0</sub>	1.2 V Decoupling pins for core logic GND. Decoupling capacitor must be connected between these pins and the nearest V <sub>DD_LV_COR0</sub> pin.	11	17	25
V <sub>DD_LV_COR1</sub>	1.2 V Decoupling pins for core logic supply. Decoupling capacitor must be connected between these pins and the nearest V <sub>SS_LV_COR1</sub> pin.	65	93	117
V <sub>SS_LV_COR1</sub>	1.2 V Decoupling pins for core logic GND. Decoupling capacitor must be connected between these pins and the nearest V <sub>DD_LV_COR1</sub> pin.	66	94	118
V <sub>DD_LV_COR2</sub>	1.2 V Decoupling pins for core logic supply. Decoupling capacitor must be connected between these pins and the nearest V <sub>SS_LV_COR2</sub> pin.	92	131	155
V <sub>SS_LV_COR2</sub>	1.2 V Decoupling pins for core logic GND. Decoupling capacitor must be connected between these pins and the nearest V <sub>DD_LV_COR2</sub> pin.	93	132	156
V <sub>DD_LV_COR3</sub>	1.2 V Decoupling pins for core logic supply. Decoupling capacitor must be connected between these pins and the nearest V <sub>SS_LV_COR3</sub> pin.	25	36	44
V <sub>SS_LV_COR3</sub>	1.2 V Decoupling pins for core logic GND. Decoupling capacitor must be connected between these pins and the nearest V <sub>DD_LV_COR3</sub> pin.	24	35	43

1. LQFP176 available only as development package.

2. See datasheet Voltage Regulator Electrical Characteristics section for more details.

## 2.2.2 System pins

[Table 6](#) and [Table 7](#) contain information on pin functions for the SPC56xP54x/SPC56xP60x devices. The pins listed in [Table 6](#) are single-function pins. The pins shown in [Table 7](#) are multi-function pins, programmable via their respective Pad Configuration Register (PCR) values.

Table 6. System pins

Symbol	Description	Direction	Pad Speed <sup>(1)</sup>		Pin		
			SRC=0	SRC=1	LQFP 100	LQFP 144	LQFP 176 <sup>(2)</sup>
Dedicated pins							
MDO0	Nexus Message Data Output—line 0	Output Only	Fast		—	9	17
MDO4	Nexus Message Data Output—line 4	Output Only	Fast		—	—	7

Table 6. System pins (continued)

Symbol	Description	Direction	Pad Speed <sup>(1)</sup>		Pin		
			SRC=0	SRC=1	LQFP 100	LQFP 144	LQFP 176 <sup>(2)</sup>
MDO5	Nexus Message Data Output—line 5	Output Only	Fast		—	—	8
MDO6	Nexus Message Data Output—line 6	Output Only	Fast		—	—	9
MDO7	Nexus Message Data Output—line 7	Output Only	Fast		—	—	110
MDO8	Nexus Message Data Output—line 8	Output Only	Fast		—	—	111
MDO9	Nexus Message Data Output—line 9	Output Only	Fast		—	—	112
MDO10	Nexus Message Data Output—line 10	Output Only	Fast		—	—	166
MDO11	Nexus Message Data Output—line 11	Output Only	Fast		—	—	171
RDY	Nexus ready output	Output Only	—	—	—	—	172
NMI	Non-Maskable Interrupt	Input Only	—	—	1	1	1
XTAL	Analog output of the oscillator amplifier circuit. Needs to be grounded if oscillator is used in bypass mode.	—	—	—	18	29	37
EXTAL	Analog input of the oscillator amplifier circuit, when the oscillator is not in bypass mode. Analog input for the clock generator when the oscillator is in bypass mode.	—	—	—	19	30	38
TMS <sup>(3)</sup>	JTAG state machine control	Input Only	—	—	59	87	105
TCK <sup>(3)</sup>	JTAG clock	Input Only	—	—	60	88	106
TDI <sup>(3)</sup>	JTAG data input	Input Only	—	—	58	86	104
TDO <sup>(3)</sup>	JTAG data output	Output Only	—	—	61	89	107
Reset pin							
$\overline{\text{RESET}}$ <sup>(4)</sup>	Bidirectional reset with Schmitt trigger characteristics and noise filter	Bidirectional	Medium	—	20	31	39
Test pin							
V <sub>PP TEST</sub>	Pin for testing purpose only. To be tied to ground in normal operating mode.	—	—	—	74	107	131
V <sub>REG_BYPASS</sub>	Pin for testing purpose only. To be tied to ground in normal operating mode.	—	—	—	34	51	59

1. SRC values refer to the value assigned to the Slew Rate Control bits of the pad configuration register.

Table 7. Pin muxing<sup>(1)</sup> (continued)

Port pin	PCR No.	Alternate function <sup>(2)</sup> , (3)	Functions	Peripheral <sup>(4)</sup>	I/O direction <sup>(5)</sup>	Pad speed <sup>(6)</sup>		Pin		
						SRC = 0	SRC = 1	LQFP 100	LQFP 144	LQFP 176 <sup>(7)</sup>
Port C										
C[0]	PCR[32]	ALT0 ALT1 ALT2 ALT3 —	GPIO[32] — — — AN[19]	SIUL — — — ADC_0	Input Only	—	—	45	66	78
C[1]	PCR[33]	ALT0 ALT1 ALT2 ALT3 —	GPIO[33] — — — AN[2]	SIUL — — — ADC_0	Input Only	—	—	28	41	49
C[2]	PCR[34]	ALT0 ALT1 ALT2 ALT3 —	GPIO[34] — — — AN[3]	SIUL — — — ADC_0	Input Only	—	—	30	45	53
C[3]	PCR[35]	ALT0 ALT1 ALT2 ALT3 —	GPIO[35] CS1_0 ETC[4] TXD EIRQ[21]	SIUL DSPI_0 eTimer_1 LINFlex_1 SIUL	I/O O I/O O I	Slow	Medium	10	16	24
C[4]	PCR[36]	ALT0 ALT1 ALT2 ALT3 —	GPIO[36] CS0_0 — DEBUG[4] EIRQ[22]	SIUL DSPI_0 — SSCM SIUL	I/O I/O — — I	Slow	Medium	5	11	19
C[5]	PCR[37]	ALT0 ALT1 ALT2 ALT3 —	GPIO[37] SCK_0 SCK_4 DEBUG[5] EIRQ[23]	SIUL DSPI_0 DSPI_4 SSCM SIUL	I/O I/O I/O — I	Slow	Medium	7	13	21
C[6]	PCR[38]	ALT0 ALT1 ALT2 ALT3 —	GPIO[38] SOUT_0 — DEBUG[6] EIRQ[24]	SIUL DSPI_0 — SSCM SIUL	I/O O — — I	Slow	Medium	98	142	174



Table 7. Pin muxing<sup>(1)</sup> (continued)

Port pin	PCR No.	Alternate function <sup>(2), (3)</sup>	Functions	Peripheral <sup>(4)</sup>	I/O direction <sup>(5)</sup>	Pad speed <sup>(6)</sup>		Pin		
						SRC = 0	SRC = 1	LQFP 100	LQFP 144	LQFP 176 <sup>(7)</sup>
Port G										
G[0]	PCR[96]	ALT0 ALT1 ALT2 ALT3 —	GPIO[96] F[0] — — EIRQ[30]	SIUL FCCU — — SIUL	I/O O — — I	Slow	Medium	—	38	46
G[1]	PCR[97]	ALT0 ALT1 ALT2 ALT3 —	GPIO[97] F[1] — — EIRQ[31]	SIUL FCCU — — SIUL	I/O O — — I	Slow	Medium	—	141	173
G[2]	PCR[98]	ALT0 ALT1 ALT2 ALT3 —	GPIO[98] — — — SIN_4	SIUL — — — DSPI_4	I/O — — — I	Slow	Medium	—	102	126
G[3]	PCR[99]	ALT0 ALT1 ALT2 ALT3	GPIO[99] — SOUT_4 —	SIUL — DSPI_4 —	I/O — O —	Slow	Medium	—	104	128
G[4]	PCR[100]	ALT0 ALT1 ALT2 ALT3	GPIO[100] — SCK_4 —	SIUL — DSPI_4 —	I/O — I/O —	Slow	Medium	—	100	124
G[5]	PCR[101]	ALT0 ALT1 ALT2 ALT3	GPIO[101] — CS0_4 —	SIUL — DSPI_4 —	I/O — I/O —	Slow	Medium	—	85	103
G[6]	PCR[102]	ALT0 ALT1 ALT2 ALT3	GPIO[102] — CS1_4 —	SIUL — DSPI_4 —	I/O — O —	Slow	Medium	—	98	122
G[7]	PCR[103]	ALT0 ALT1 ALT2 ALT3	GPIO[103] — CS2_4 —	SIUL — DSPI_4 —	I/O — O —	Slow	Medium	—	83	101

### 3.3 Absolute maximum ratings

Table 9. Absolute maximum ratings<sup>(1)</sup>

Symbol		Parameter	Conditions	Min	Max <sup>(2)</sup>	Unit
$V_{SS\_HV}$	SR	Digital ground	—	0	0	V
$V_{DD\_HV\_IOx}^{(3)}$	SR	3.3 V / 5.0 V input/output supply voltage with respect to ground ( $V_{SS\_HV}$ )	—	−0.3	6.0	V
$V_{SS\_HV\_IOx}$	SR	Input/output ground voltage with respect to ground ( $V_{SS\_HV}$ )	—	−0.1	0.1	V
$V_{DD\_HV\_FL}$	SR	3.3 V / 5.0 V code and data flash memory supply voltage with respect to ground ( $V_{SS\_HV}$ )	—	−0.3	6.0	V
			Relative to $V_{DD\_HV\_IOx}$	−0.3	$V_{DD\_HV\_IOx} + 0.3$	
$V_{SS\_HV\_FL}$	SR	Code and data flash memory ground with respect to ground ( $V_{SS\_HV}$ )	—	−0.1	0.1	V
$V_{DD\_HV\_OSC}$	SR	3.3 V / 5.0 V crystal oscillator amplifier supply voltage with respect to ground ( $V_{SS\_HV}$ )	—	−0.3	6.0	V
			Relative to $V_{DD\_HV\_IOx}$	−0.3	$V_{DD\_HV\_IOx} + 0.3$	
$V_{SS\_HV\_OSC}$	SR	3.3 V / 5.0 V crystal oscillator amplifier reference voltage with respect to ground ( $V_{SS\_HV}$ )	—	−0.1	0.1	V
$V_{DD\_HV\_REG}$	SR	3.3 V / 5.0 V voltage regulator supply voltage with respect to ground ( $V_{SS\_HV}$ )	—	−0.3	6.0	V
			Relative to $V_{DD\_HV\_IOx}$	−0.3	$V_{DD\_HV\_IOx} + 0.3$	
$V_{DD\_HV\_AD}$	SR	3.3 V / 5.0 V ADC supply and high reference voltage with respect to ground ( $V_{SS\_HV}$ )	$V_{DD\_HV\_REG} < 2.7\text{ V}$	−0.3	$V_{DD\_HV\_REG} + 0.3$	V
			$V_{DD\_HV\_REG} > 2.7\text{ V}$	−0.3	6.0	
$V_{SS\_HV\_AD}$	SR	ADC ground and low reference voltage with respect to ground ( $V_{SS\_HV}$ )	—	−0.1	0.1	V
$TV_{DD}$	SR	Slope characteristics on all $V_{DD}$ during power up <sup>(4)</sup> with respect to ground ( $V_{SS\_HV}$ )	—	3.0 <sup>(5)</sup>	$500 \times 10^3$ (0.5 [V/μs])	V/s
$V_{IN}$	SR	Voltage on any pin with respect to ground ( $V_{SS\_HV\_IOx}$ ) with respect to ground ( $V_{SS\_HV}$ )	—	−0.3	6.0	V
			Relative to $V_{DD\_HV\_IOx}$	−0.3	$V_{DD\_HV\_IOx} + 0.3$	
$V_{INAN}$	SR	Analog input voltage	$V_{DD\_HV\_REG} < 2.7\text{ V}$	$V_{SS\_HV\_AD} - 0.3$	$V_{DD\_HV\_AD} + 0.3$	V
			$V_{DD\_HV\_REG} > 2.7\text{ V}$	$V_{SS\_HV\_AD}$	$V_{DD\_HV\_AD}$	V
$I_{INJPAD}$	SR	Injected input current on any pin during overload condition	—	−10	10	mA

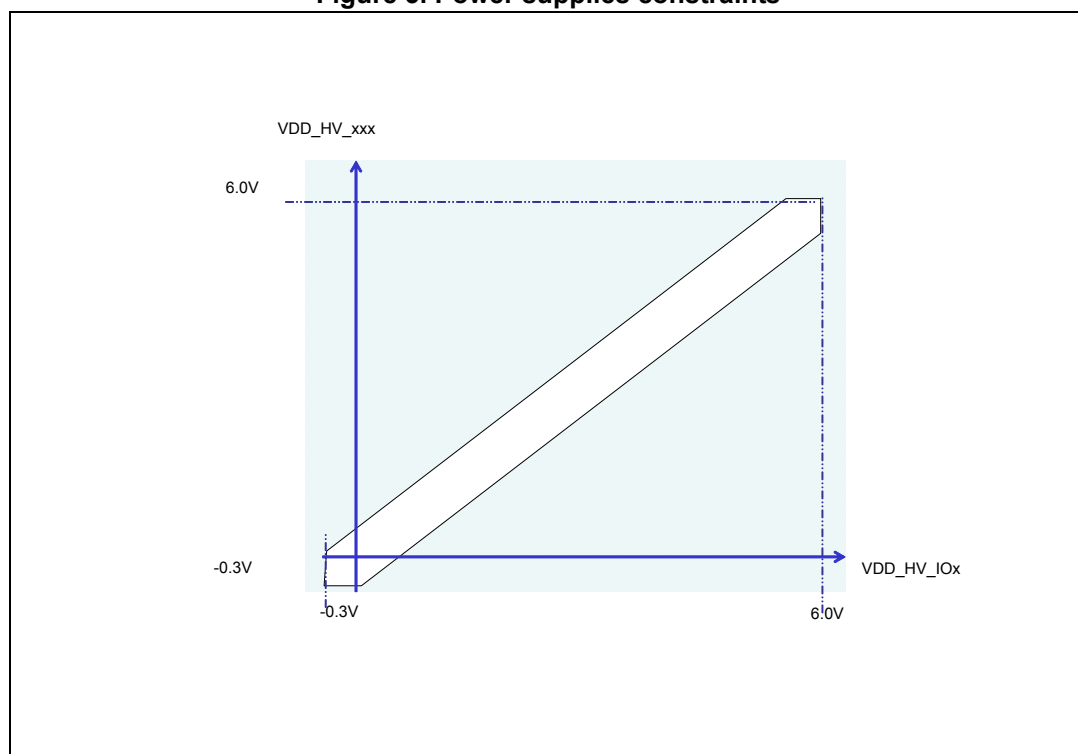
Table 9. Absolute maximum ratings<sup>(1)</sup> (continued)

Symbol		Parameter	Conditions	Min	Max <sup>(2)</sup>	Unit
$I_{INJSUM}$	SR	Absolute sum of all injected input currents during overload condition	—	–50	50	mA
$I_{VDD\_LV}$	SR	Low voltage static current sink through $V_{DD\_LV}$	—	—	155	mA
$T_{STG}$	SR	Storage temperature	—	–55	150	°C
$T_J$	SR	Junction temperature under bias	—	–40	150	°C

- Functional operating conditions are given in the DC electrical characteristics. Absolute maximum ratings are stress ratings only, and functional operation at the maxima is not guaranteed. Stress beyond the listed maxima may affect device reliability or cause permanent damage to the device.
- Absolute maximum voltages are currently maximum burn-in voltages. Absolute maximum specifications for device stress have not yet been determined.
- The difference between each couple of voltage supplies must be less than 300 mV,  $|V_{DD\_HV\_IOy} - V_{DD\_HV\_IOx}| < 300$  mV.
- Guaranteed by device validation.
- Minimum value of  $TV_{DD}$  must be guaranteed until  $V_{DD\_HV\_REG}$  reaches 2.6 V (maximum value of  $V_{PORH}$ ).

Figure 5 shows the constraints of the different power supplies.

Figure 5. Power supplies constraints



The SPC56xP54x/SPC56xP60x supply architecture provides an ADC supply that is managed independently of standard  $V_{DD\_HV}$  supply. Figure 6 shows the constraints of the ADC power supply.

$R_{\theta JC}$  is device related and cannot be influenced by the user. The user controls the thermal environment to change the case to ambient thermal resistance,  $R_{\theta CA}$ . For instance, the user can change the size of the heat sink, the air flow around the device, the interface material, the mounting arrangement on printed circuit board, or change the thermal dissipation on the printed circuit board surrounding the device.

To determine the junction temperature of the device in the application when heat sinks are not used, the Thermal Characterization Parameter ( $\Psi_{JT}$ ) can be used to determine the junction temperature with a measurement of the temperature at the top center of the package case using [Equation 3](#):

**Equation 3**  $T_J = T_T + (\Psi_{JT} \times P_D)$

where:

$T_T$  = thermocouple temperature on top of the package (°C)

$\Psi_{JT}$  = thermal characterization parameter (°C/W)

$P_D$  = power dissipation in the package (W)

The thermal characterization parameter is measured per JESD51-2 specification using a 40 gauge type T thermocouple epoxied to the top center of the package case. The thermocouple should be positioned so that the thermocouple junction rests on the package. A small amount of epoxy is placed over the thermocouple junction and over about 1 mm of wire extending from the junction. The thermocouple wire is placed flat against the package case to avoid measurement errors caused by cooling effects of the thermocouple wire.

### 3.5.1.1 References

Semiconductor Equipment and Materials International  
3081 Zanker Road  
San Jose, CA 95134 U.S.A.  
(408) 943-6900

MIL-SPEC and EIA/JESD (JEDEC) specifications are available from Global Engineering Documents at 800-854-7179 or 303-397-7956.

JEDEC specifications are available on the WEB at [jedec.org](http://jedec.org) web site.

1. C.E. Triplett and B. Joiner, *An Experimental Characterization of a 272 PBGA Within an Automotive Engine Controller Module*, Proceedings of SemiTherm, San Diego, 1998, pp. 47-54.
2. G. Kromann, S. Shidore, and S. Addison, *Thermal Modeling of a PBGA for Air-Cooled Applications*, Electronic Packaging and Production, pp. 53-58, March 1998.
3. B. Joiner and V. Adams, *Measurement and Simulation of Junction to Board Thermal Resistance and Its Application in Thermal Modeling*, Proceedings of SemiTherm, San Diego, 1999, pp. 212-220.

### 3.6 Electromagnetic interference (EMI) characteristics

Table 14. EMI testing specifications

Parameter	Symbol	Conditions	$f_{OSC}/f_{BUS}$	Frequency	Level (Max)	Unit
$V_{RE\_TEM}$	Radiated emissions, electric field	$V_{DD} = 5\text{ V};$ $T_A = 25\text{ °C}$  150 kHz–30 MHz RBW 9 kHz, Step Size 5 kHz	8 MHz crystal 64 MHz bus No PLL frequency modulation	150 kHz–150 MHz	18	dB $\mu$ V
				150–1000 MHz	12	
				IEC Level	M	—
		30 MHz–1 GHz RBW 120 kHz, Step Size 80 kHz	8 MHz crystal 64 MHz bus $\pm 2\%$ PLL frequency modulation	150 kHz–150 MHz	18	dB $\mu$ V
				150–1000 MHz	12	
				IEC Level	M	—

### 3.7 Electrostatic discharge (ESD) characteristics

Table 15. ESD ratings<sup>(1)(2)</sup>

Symbol	Parameter	Conditions	Value	Unit
$V_{ESD(HBM)}$	SR Electrostatic discharge (Human Body Model)	—	2000	V
$V_{ESD(CDM)}$	SR Electrostatic discharge (Charged Device Model)	—	750 (corners)	V
			500 (other)	

1. All ESD testing is in conformity with CDF-AEC-Q100 Stress Test Qualification for Automotive Grade Integrated Circuits.
2. A device will be defined as a failure if after exposure to ESD pulses the device no longer meets the device specification requirements. Complete DC parametric and functional testing shall be performed per applicable device specification at room temperature followed by hot temperature, unless specified otherwise in the device specification.

### 3.8 Power management electrical characteristics

#### 3.8.1 Voltage regulator electrical characteristics

The internal voltage regulator requires an external NPN ballast to be connected as shown in [Figure 9](#). [Table 16](#) contains all approved NPN ballast components. Capacitances should be placed on the board as near as possible to the associated pins. Care should also be taken to limit the serial inductance of the  $V_{DD\_HV\_REG}$ , BCTRL and  $V_{DD\_LV\_CORx}$  pins to less than  $L_{Reg}$ , see [Table 17](#).

**Note:** The voltage regulator output cannot be used to drive external circuits. Output pins are used only for decoupling capacitances.

$V_{DD\_LV\_COR}$  must be generated using internal regulator and external NPN transistor. It is not possible to provide  $V_{DD\_LV\_COR}$  through external regulator.

For the SPC56xP54x/SPC56xP60x microcontroller, capacitors, with total values not below  $C_{DEC1}$ , should be placed between  $V_{DD\_LV\_CORx}/V_{SS\_LV\_CORx}$  close to external ballast transistor emitter. 4 capacitors, with total values not below  $C_{DEC2}$ , should be placed close to microcontroller pins between each  $V_{DD\_LV\_CORx}/V_{SS\_LV\_CORx}$  supply pairs and the

Table 18. Low voltage monitor electrical characteristics

Symbol		Parameter	Conditions <sup>(1)</sup>	Value		Unit
				Min	Max	
V <sub>PORH</sub>	T	Power-on reset threshold	—	1.5	2.7	V
V <sub>PORUP</sub>	P	Supply for functional POR module	T <sub>A</sub> = 25°C	1.0	—	V
V <sub>REGLVDMOK_H</sub>	P	Regulator low voltage detector high threshold	—	—	2.95	V
V <sub>REGLVDMOK_L</sub>	P	Regulator low voltage detector low threshold	—	2.6	—	V
V <sub>FLLVDMOK_H</sub>	P	Flash memory low voltage detector high threshold	—	—	2.95	V
V <sub>FLLVDMOK_L</sub>	P	Flash memory low voltage detector low threshold	—	2.6	—	V
V <sub>IOLVDMOK_H</sub>	P	I/O low voltage detector high threshold	—	—	2.95	V
V <sub>IOLVDMOK_L</sub>	P	I/O low voltage detector low threshold	—	2.6	—	V
V <sub>IOLVDM5OK_H</sub>	P	I/O 5V low voltage detector high threshold	—	—	4.4	V
V <sub>IOLVDM5OK_L</sub>	P	I/O 5V low voltage detector low threshold	—	3.8	—	V
V <sub>MLVDDOK_H</sub>	P	Digital supply low voltage detector high	—	—	1.15	V
V <sub>MLVDDOK_L</sub>	P	Digital supply low voltage detector low	—	1.08	—	V

1. V<sub>DD</sub> = 3.3V ± 10% / 5.0V ± 10%, T<sub>A</sub> = -40 °C to T<sub>A</sub> MAX, unless otherwise specified.

### 3.9 Power Up/Down sequencing

To prevent an overstress event or a malfunction within and outside the device, the SPC56xP54x/SPC56xP60x implements the following sequence to ensure each module is started only when all conditions for switching it ON are available:

1. A POWER\_ON module working on voltage regulator supply controls the correct start-up of the regulator. This is a key module ensuring safe configuration for all voltage regulator functionality when supply is below 1.5V. Associated POWER\_ON (or POR) signal is active low.
  - Several low voltage detectors, working on voltage regulator supply monitor the voltage of the critical modules (voltage regulator, I/Os, flash memory and low voltage domain). LVDs are gated low when POWER\_ON is active.
  - A POWER\_OK signal is generated when all critical supplies monitored by the LVD are available. This signal is active high and released to all modules including I/Os, flash memory and RC16 oscillator needed during power-up phase and reset phase. When POWER\_OK is low the associated modules are set into a safe state.

Table 22. DC electrical characteristics (3.3 V, NVUSRO[PAD3V5V]=1)<sup>(1)</sup> (continued)

Symbol		Parameter	Conditions	Min	Max	Unit
$I_{PD}$	P	Equivalent pull-down current	$V_{IN} = V_{IL}$	10	—	$\mu A$
			$V_{IN} = V_{IH}$	—	130	
$I_{IL}$	P	Input leakage current (all bidirectional ports)	$T_A = -40$ to $125\text{ }^{\circ}C$	—	1	$\mu A$
$I_{IL}$	P	Input leakage current (all ADC input-only ports)	$T_A = -40$ to $125\text{ }^{\circ}C$	—	0.5	$\mu A$
$C_{IN}$	D	Input capacitance	—	—	10	pF
$I_{PU}$	D	$\overline{RESET}$ , equivalent pull-up current	$V_{IN} = V_{IL}$	-130	—	$\mu A$
			$V_{IN} = V_{IH}$	—	-10	
$I_{PD}$	D	$\overline{RESET}$ , equivalent pull-down current	$V_{IN} = V_{IL}$	10	—	$\mu A$
			$V_{IN} = V_{IH}$	—	130	

1. These specifications are design targets and subject to change per device characterization.

2. "SR" parameter values must not exceed the absolute maximum ratings shown in [Table 9](#).

Table 24. Peripherals supply current (5 V and 3.3 V)<sup>(1)</sup>

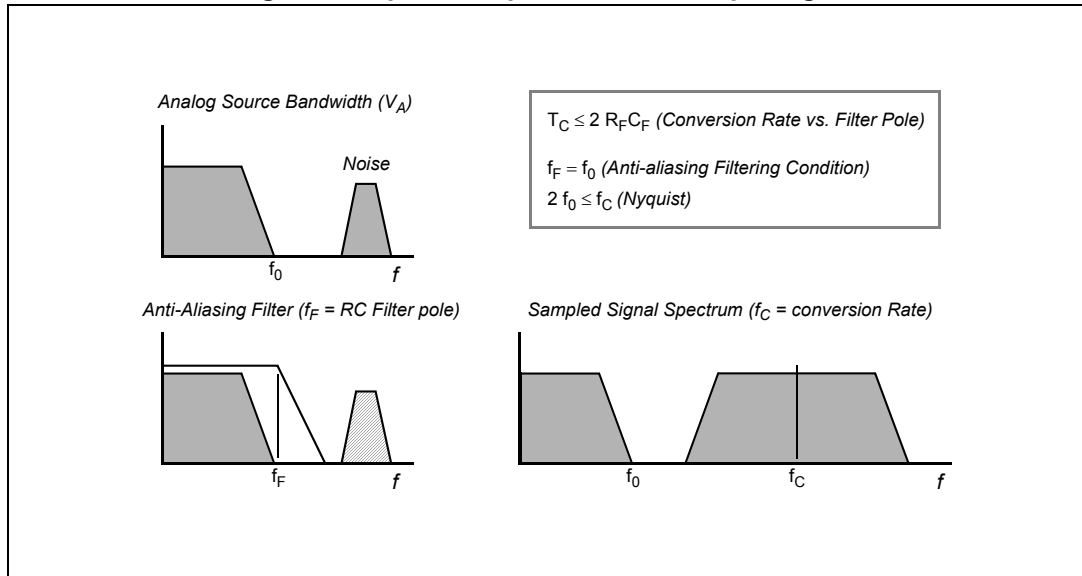
Symbol	Parameter	Conditions	Value		Unit
			Typ	Max	
$I_{DD\_HV(CAN)}$	T CAN (FlexCAN) supply current on VDD_HV_REG	500 Kbyte/s Total (static + dynamic) consumption: – FlexCAN in loop-back mode – XTAL@ 8 MHz used as CAN engine clock source – Message sending period is 580 $\mu$ s	$21.6 * f_{periph}$	$28.1 * f_{periph}$	$\mu$ A
$I_{DD\_HV(SCI)}$	T SCI (LINFlex) supply current on VDD_HV_REG	Total (static + dynamic) consumption: – LIN mode – Baudrate: 115.2 Kbyte/s	$10.8 * f_{periph}$	$14.1 * f_{periph}$	
$I_{DD\_HV(SPI)}$	T SPI (DSPI) supply current on VDD_HV_REG	Ballast dynamic consumption (continuous communication): – Baudrate: 2 Mbit/s – Transmission every 8 $\mu$ s – Frame: 16 bits	$4.8 * f_{periph}$	$6.3 * f_{periph}$	
$I_{DD\_HV(ADC)}$	T ADC supply current on VDD_HV_REG	VDD = 5.5 V Ballast dynamic consumption (continuous conversion)	$120 * f_{periph}$	$156 * f_{periph}$	mA
$I_{DD\_HV\_ADC(ADC)}$	T ADC supply current on VDD_HV_ADC	VDD = 5.5 V Analog dynamic consumption (continuous conversion)	$0.005 * f_{periph} + 2.8$	$0.007 * f_{periph} + 3.4$	
$I_{DD\_HV(eTimer)}$	T eTimer supply current on VDD_HV_REG	PWM signals generation on all 1 channel @10kHz Dynamic consumption does not change varying the frequency	1.8	2.4	mA
$I_{DD\_HV(FlexRay)}$	T FlexRay supply current on VDD_HV_REG	Static consumption	$4.2 * f_{periph}$	$5.5 * f_{periph}$	$\mu$ A

1. Operating conditions:  $f_{periph}$  = 8 MHz to 64 MHz



$C_S$  with respect to the ideal source  $V_A$ ; the time constant  $R_F C_F$  of the filter is very high with respect to the sampling time ( $T_S$ ). The filter is typically designed to act as anti-aliasing.

**Figure 19. Spectral representation of input signal**



Calling  $f_0$  the bandwidth of the source signal (and as a consequence the cut-off frequency of the anti-aliasing filter,  $f_F$ ), according to the Nyquist theorem the conversion rate  $f_C$  must be at least  $2f_0$ ; it means that the constant time of the filter is greater than or at least equal to twice the conversion period ( $T_C$ ). Again the conversion period  $T_C$  is longer than the sampling time  $T_S$ , which is just a portion of it, even when fixed channel continuous conversion mode is selected (fastest conversion rate at a specific channel): in conclusion it is evident that the time constant of the filter  $R_F C_F$  is definitively much higher than the sampling time  $T_S$ , so the charge level on  $C_S$  cannot be modified by the analog signal source during the time in which the sampling switch is closed.

The considerations above lead to impose new constraints on the external circuit, to reduce the accuracy error due to the voltage drop on  $C_S$ ; from the two charge balance equations above, it is simple to derive [Equation 11](#) between the ideal and real sampled voltage on  $C_S$ :

**Equation 11**

$$\frac{V_A}{V_{A2}} = \frac{C_{P1} + C_{P2} + C_F}{C_{P1} + C_{P2} + C_F + C_S}$$

From this formula, in the worst case (when  $V_A$  is maximum, that is for instance 5 V), assuming to accept a maximum error of half a count, a constraint is evident on  $C_F$  value:

**Equation 12**

$$C_F > 2048 \times C_S$$

Table 39. Nexus debug port timing<sup>(1)</sup> (continued)

No.	Symbol		C	Parameter	Value			Unit
					Min	Typ	Max	
6	$t_{\text{NTDIS}}$	CC	D	TDI data setup time	6	—	—	ns
	$t_{\text{NTMSS}}$	CC	D	TMS data setup time	6	—	—	ns
7	$t_{\text{NTDIH}}$	CC	D	TDI data hold time	10	—	—	ns
	$t_{\text{NTMSH}}$	CC	D	TMS data hold time	10	—	—	ns
8	$t_{\text{TDOV}}$	CC	D	TCK low to TDO data valid	—	—	35	ns
9	$t_{\text{TDOI}}$	CC	D	TCK low to TDO data invalid	6	—	—	ns

1. All values need to be confirmed during device validation.
2. Lower frequency is required to be fully compliant to standard.

Figure 25. Nexus output timing

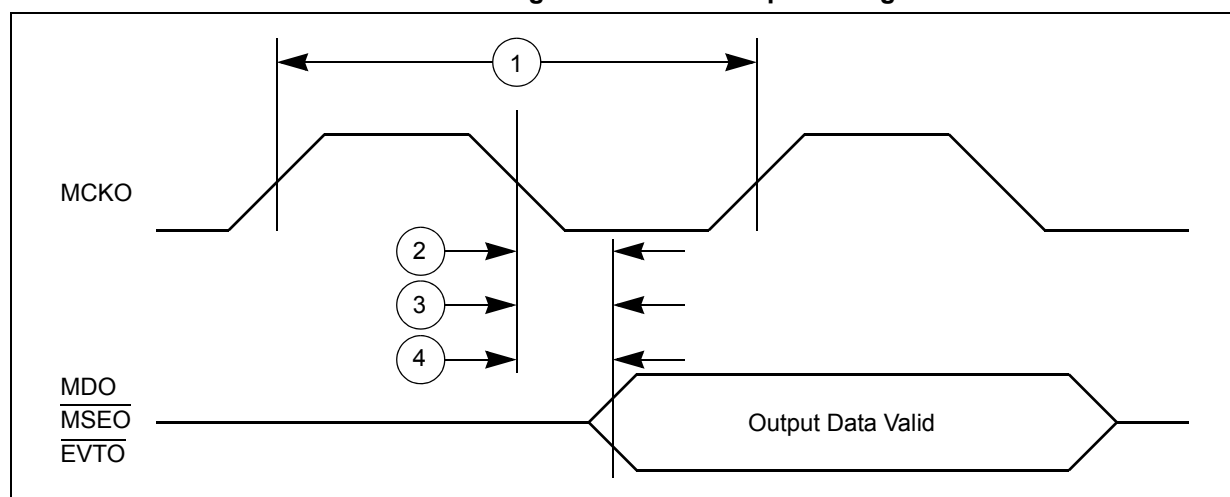


Figure 26. Nexus event trigger and test clock timings

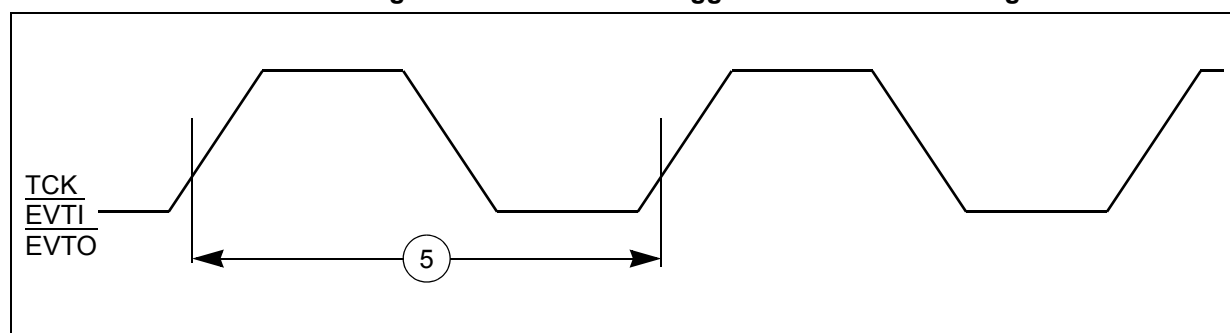
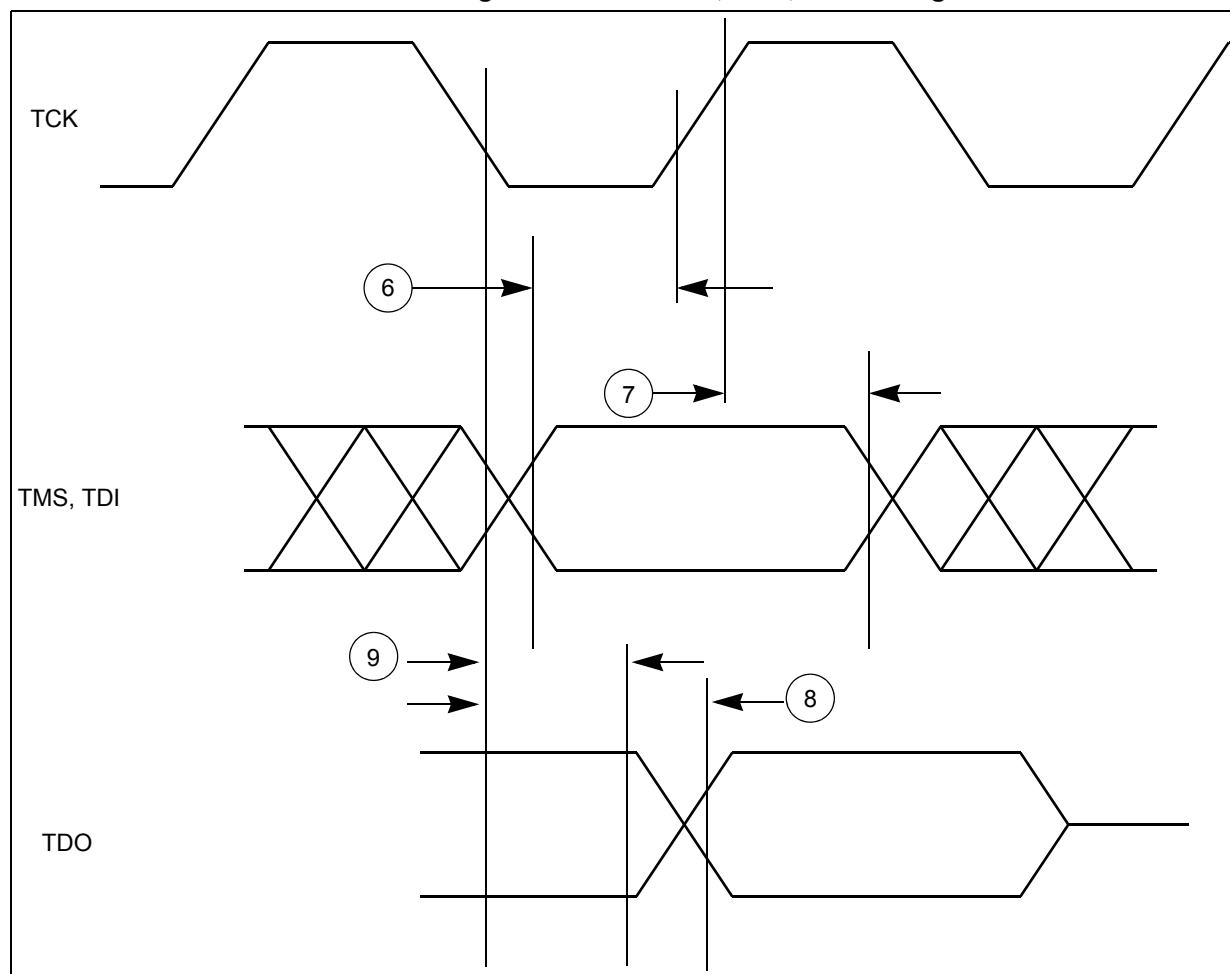


Figure 27. Nexus TDI, TMS, TDO timing



### 3.18.4 External interrupt timing (IRQ pin)

Table 40. External interrupt timing<sup>(1)</sup>

No.	Symbol	C	Parameter	Conditions	Min	Max	Unit
1	$t_{IPWL}$	CC	D	IRQ pulse width low	—	4	$t_{CYC}$
2	$t_{IPWH}$	CC	D	IRQ pulse width high	—	4	$t_{CYC}$
3	$t_{ICYC}$	CC	D	IRQ edge to edge time <sup>(2)</sup>	—	$4 + N^{(3)}$	$t_{CYC}$

1. IRQ timing specified at  $f_{SYS} = 64$  MHz and  $V_{DD\_HV\_IOx} = 3.0$  V to 5.5 V,  $T_A = T_L$  to  $T_H$ , and  $CL = 200$  pF with  $SRC = 0b00$ .

2. Applies when IRQ pins are configured for rising edge or falling edge events, but not both.

3.  $N$  = ISR time to clear the flag.

Figure 32. DSPI classic SPI timing — slave, CPHA = 1

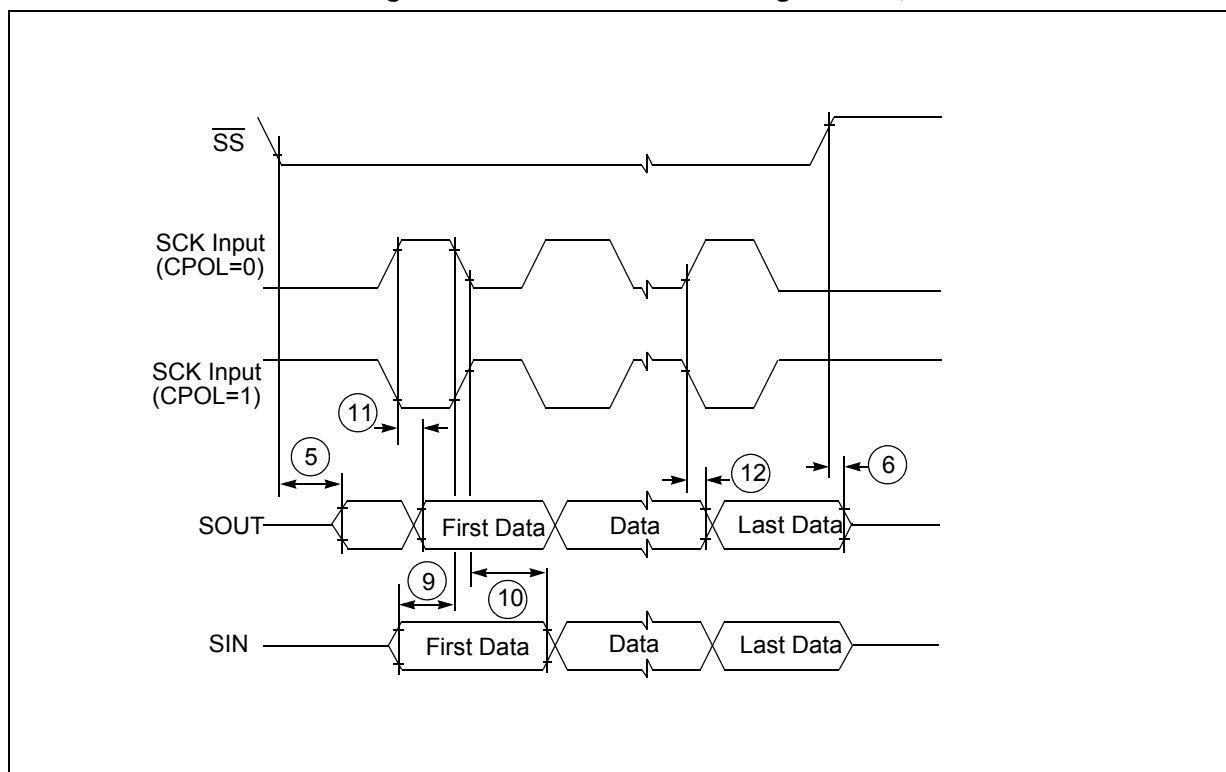


Figure 33. DSPI modified transfer format timing — master, CPHA = 0

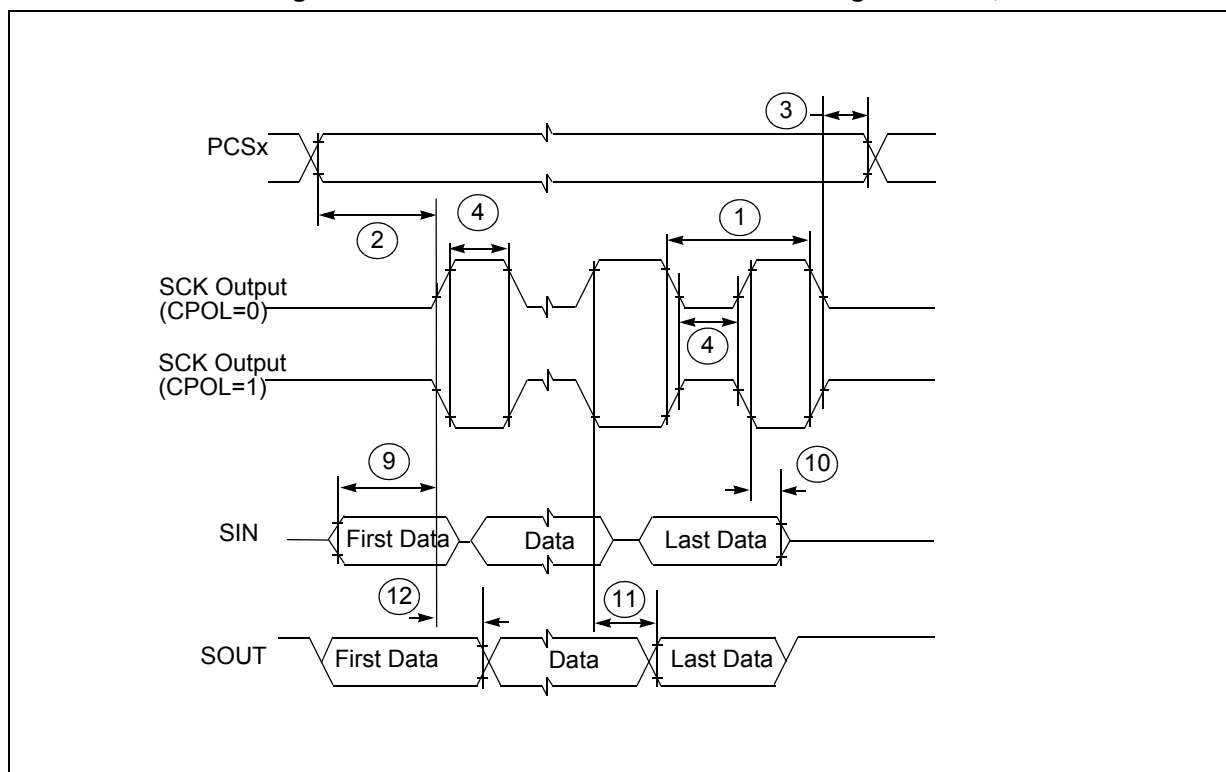


Figure 34. DSPI modified transfer format timing — master, CPHA = 1

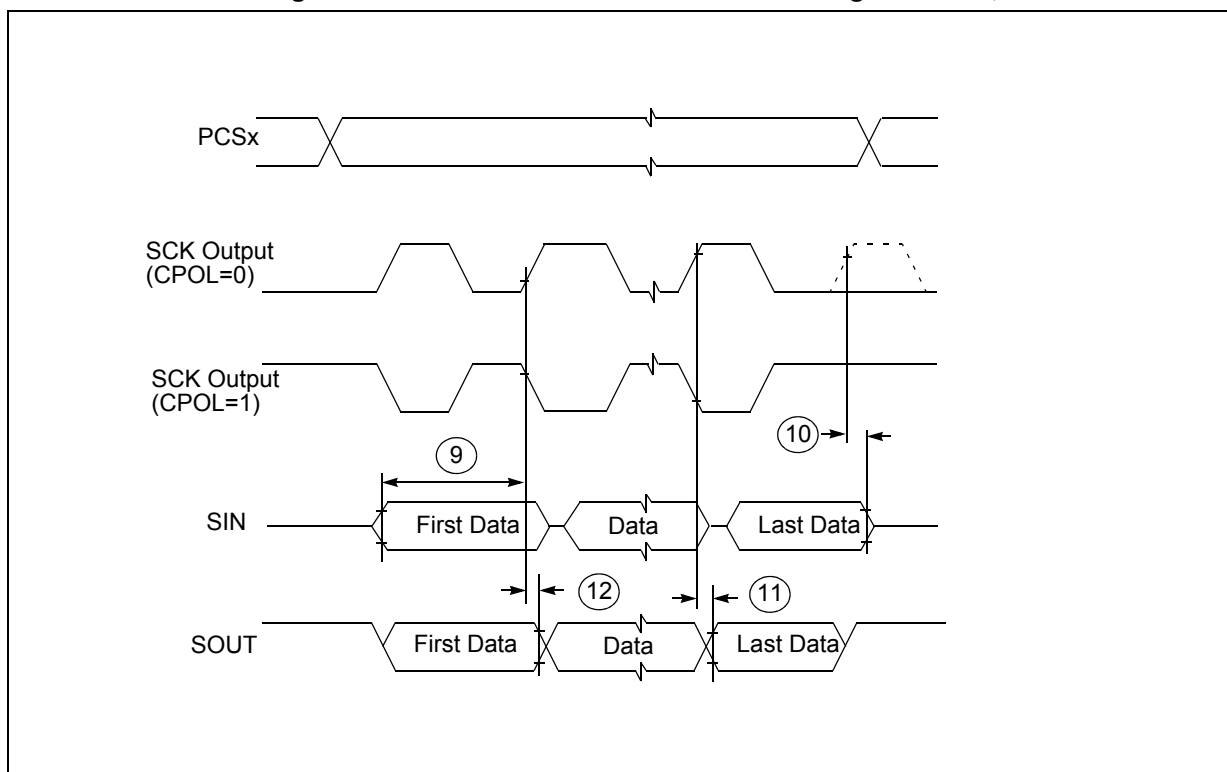


Figure 35. DSPI modified transfer format timing — slave, CPHA = 0

